

50A02CH

Bipolar Transistor

–50V, –0.5A, Low VCE(sat), PNP Single



ON Semiconductor®

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Features

- High Collector Current Capability
- Low Collector to Emitter Saturation Voltage (Resistance):
RCE(sat) typ=210mΩ [IC=0.5A, IB=50mA]
- Low ON-Resistance (Ron)
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

- Low-Frequency Amplifier
- High Speed Switching
- Small Motor Drive
- Muting Circuit

SPECIFICATIONS

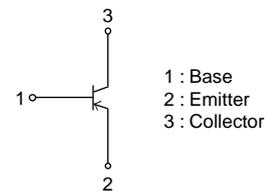
ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit
Collector to Base Voltage	VCBO	–50	V
Collector to Emitter Voltage	VCEO	–50	V
Emitter to Base Voltage	VEBO	–5	V
Collector Current	IC	–500	mA
Collector Current (Pulse)	ICP	–1.0	A
Collector Dissipation (Note 2)	PC	700	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

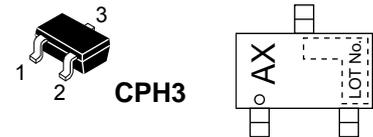
Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note 2 : Surface mounted on ceramic substrate(600mm² × 0.8mm)

ELECTRICAL CONNECTION



MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

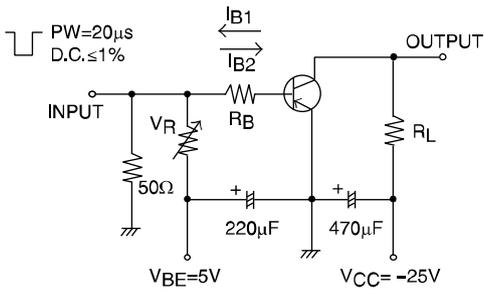
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ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	V _{CB} =-40V, I _E =0A			-100	nA
Emitter Cutoff Current	IEBO	V _{EB} =-4V, I _C =0A			-100	nA
DC Current Gain	h _{FE}	V _{CE} =-2V, I _C =-10mA	200		500	
Gain-Bandwidth Product	f _T	V _{CE} =-10V, I _C =-50mA		690		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz		3.8		pF
Collector to Emitter Saturation Voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA		-60	-120	mV
Base to Emitter Saturation Voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA		-0.9	-1.2	V
Collector to Base Breakdown Voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0A	-50			V
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-1mA, R _{BE} =∞	-50			V
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0A	-5			V
Turn-On Time	t _{on}	See specified Test Circuit		30		ns
Storage Time	t _{stg}			170		ns
Fall Time	t _f			30		ns

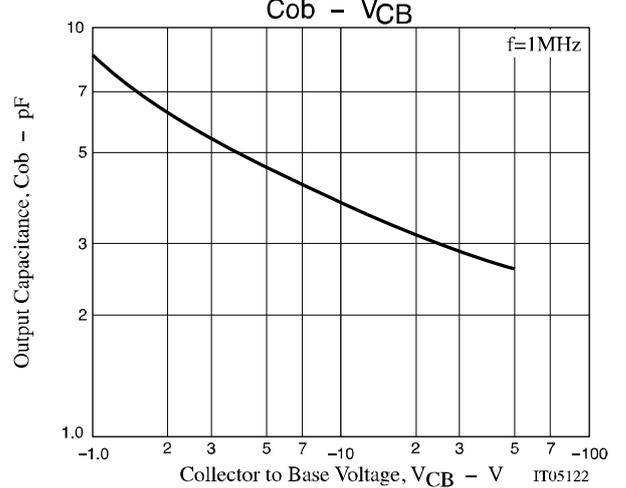
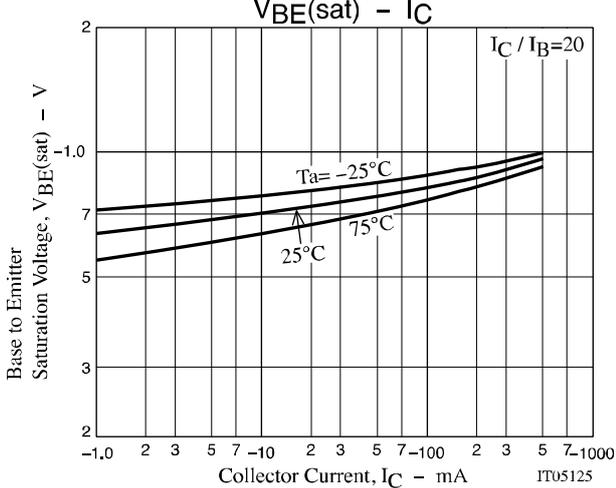
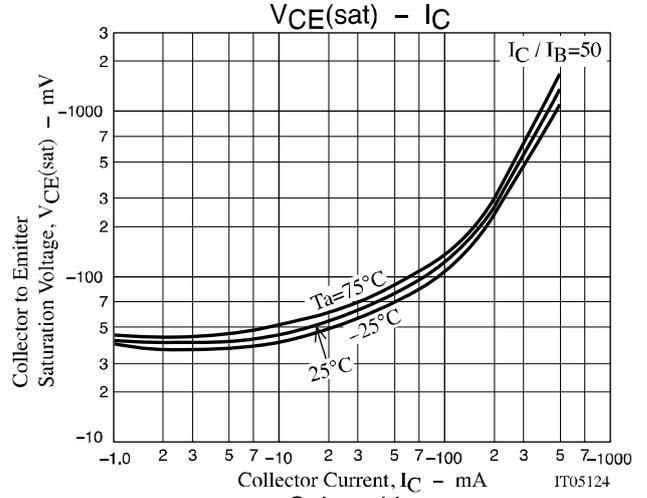
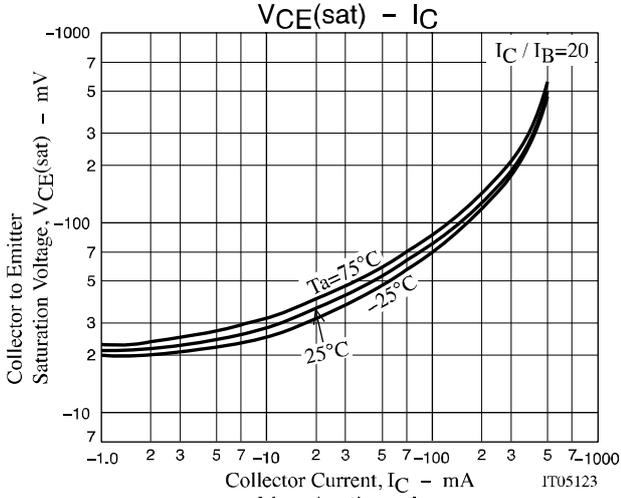
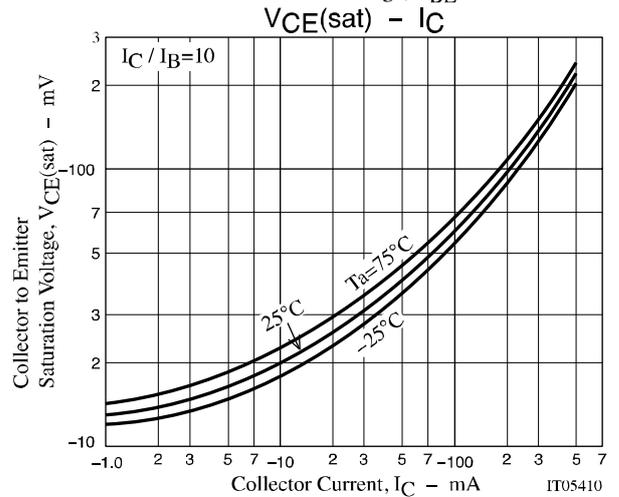
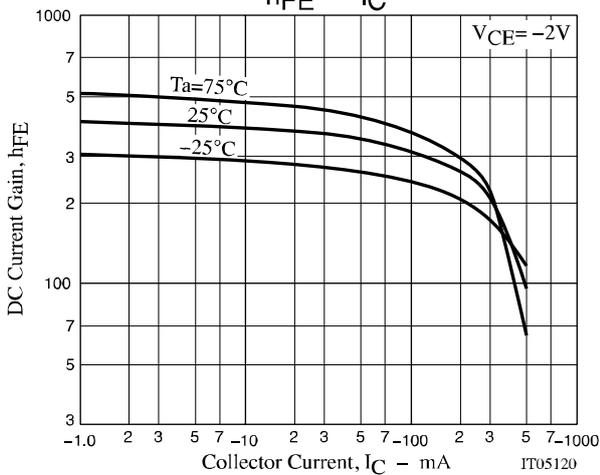
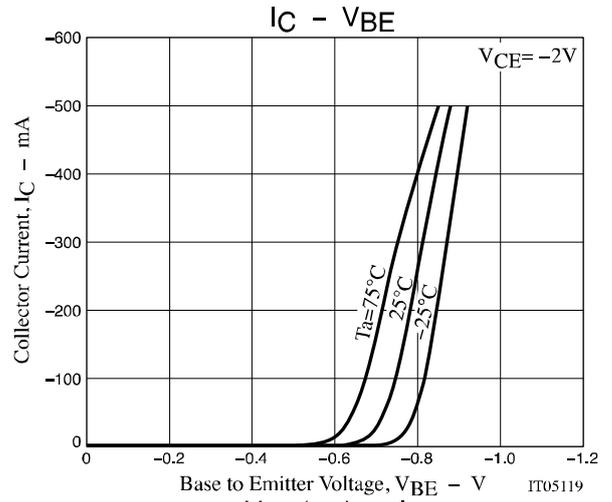
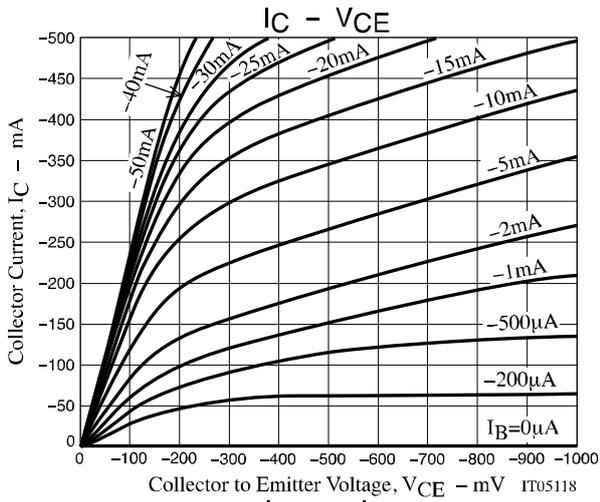
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



$$I_C = 20I_{B1} = -20I_{B2} = -200\text{mA}$$

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